

Analysis of barrier inhomogeneities of P-type Al/4H-SiC Schottky barrier diodes

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Analysis of deep level centers in GaAs pin-diode structures

Korolkov, Oleg; Toompuu, Jana; Rang, Toomas Elektronika ir elektrotehnika = Electronics and electrical engineering 2013 / [4 p.] : ill <https://doi.org/10.5755/j01.eee.19.10.5903> [Journal metrics at Scopus](#) [Article at Scopus](#) [Journal metrics at WOS](#) [Article at WOS](#)

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Change in the parameters of electron-irradiated 4H-SiC Schottky diodes as a function of the time during low-temperature isothermal annealing

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Comparative characteristics of diffusion-welded high-voltage stacks and connected in series Schottky diodes

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Comparative investigation of the graphene-on-silicon carbide and CVD graphene as a basis for biosensor application

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Comparative results of low temperature annealing of lightly doped n-layers of silicon carbide irradiated by protons and electrons

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Low-temperature annealing of lightly doped n-4H-SiC layers after irradiation with fast electrons

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Method of samples preparation intended for research of deep centers in i-, n-, and p-layers of GaAs p⁺-pin-n⁺ structures and result of analysis

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SiC JBS diode symmetrical voltage doubler represented as the diffusion-welded stack

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The specificity of solid-phase interaction of aluminium with silicon carbide in the manufacture of diffusion-welded contacts to semiconductor devices

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